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**July 2015** 

# FGA3060ADF 600 V, 30 A Field Stop Trench IGBT

#### **Features**

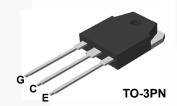
- Maximum Junction Temperature : T<sub>J</sub> = 175°C
- · Positive Temperaure Co-efficient for Easy Parallel Operating
- · High Current Capability
- Low Saturation Voltage:  $V_{CE(sat)} = 1.8 \text{ V(Typ.)} @ I_C = 30 \text{ A}$
- 100% of the Parts Tested for I<sub>LM</sub>(1)
- · High Input Impedance
- Fast Switching
- · Tighten Parameter Distribution
- RoHS Compliant

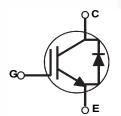
### **General Description**

This ADF IGBT series adopted Field Stop Trench 3rd generation IGBT which offer extreme low Vce(sat) and much faster switching characteristics for outstanding efficiency. And this kind of technology is fully optimized to variety PFC (Power Factor Correction) topology; Single boost, Multi channel interleaved etc with over 20KHz switching performance. TO3P package provide Super Low thermal resistance for much wider SOA for system stability.

### **Applications**

PFC topology for Home appliance: Single Boost, Multi channel Interleaved etc.





### **Absolute Maximum Ratings**

Symbol	Description		FGA3060ADF	Unit
V <sub>CES</sub>	Collector to Emitter Voltage		600	V
M	Gate to Emitter Voltage		± 20	V
$V_{GES}$	Transient Gate to Emitter Voltage		± 30	V
l <sub>o</sub>	Collector Current	@ T <sub>C</sub> = 25°C	60	Α
IC	Collector Current	@ T <sub>C</sub> = 100°C	30	Α
I <sub>LM (1)</sub>	Pulsed Collector Current	@ T <sub>C</sub> = 25°C	90	Α
I <sub>CM (2)</sub>	Pulsed Collector Current		90	Α
I <sub>F (3)</sub>	Diode Forward Current	@ T <sub>C</sub> = 25°C	3	А
	Diode Forward Current	@ T <sub>C</sub> = 100°C	1.5	А
I <sub>FM (2)</sub>	Pulsed Diode Maximum Forward Current		6	А
P <sub>D</sub>	Maximum Power Dissipation	@ T <sub>C</sub> = 25°C	176	W
י ט	Maximum Power Dissipation	@ T <sub>C</sub> = 100°C	88	W
T <sub>J</sub>	Operating Junction Temperature		-55 to +175	°C
T <sub>stg</sub>	Storage Temperature Range		-55 to +175	°C
T <sub>L</sub>	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

#### Notes

- 1.  $V_{CC}$  = 400 V,  $V_{GE}$  = 15 V,  $I_{C}$  = 90 A,  $R_{G}$  = 120  $\Omega$ , Inductive Load.
- 2. Repetitive rating: Pulse width limited by max. junction temperature.
- 3. The purpose of diode is protection for negative voltage.

### **Thermal Characteristics**

Symbol	Parameter	FGA3060ADF	Unit
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction to Case, Max.	0.85	°C/W
$R_{\theta JC}(Diode)$	Thermal Resistance, Junction to Case, Max.	5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	°C/W

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FGA3060ADF	FGA3060ADF	TO-3PN	Tube	-	-	30

# Electrical Characteristics of the IGBT $T_C = 25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	eteristics					
BV <sub>CES</sub>	Collector to Emitter Breakdown Voltage	$V_{GE} = 0 \text{ V}, I_{C} = 1 \text{ mA}$	600	-	-	V
ΔBV <sub>CES</sub> / ΔT <sub>J</sub>	Temperature Coefficient of Breakdown Voltage	I <sub>C</sub> = 1 mA, Reference to 25°C	-	0.52	-	V/°C
I <sub>CES</sub>	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0 V$	-	-	250	μА
I <sub>GES</sub>	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0 V$	-	-	±400	nA
On Charac	eteristics					
V <sub>GE(th)</sub>	G-E Threshold Voltage	$I_C$ = 30 mA, $V_{CE}$ = $V_{GE}$	4.1	5.6	7.6	V
5=(0.7)		I <sub>C</sub> = 30 A, V <sub>GE</sub> = 15 V	-	1.8	2.3	V
V <sub>CE(sat)</sub>	Collector to Emitter Saturation Voltage	I <sub>C</sub> = 30 A, V <sub>GE</sub> = 15 V, T <sub>C</sub> = 175°C	-	2.4	-	V
Dynamic C	Characteristics					
C <sub>ies</sub>	Input Capacitance		-	1072	-	pF
C <sub>oes</sub>	Output Capacitance	$V_{CE} = 30 \text{ V}, V_{GE} = 0 \text{ V},$ f = 1MHz	-	36	-	pF
C <sub>res</sub>	Reverse Transfer Capacitance	- 1 - 1101112	-	13	-	pF
Switching	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time		-	12	-	ns
t <sub>r</sub>	Rise Time		_	19.2	- /	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{CC} = 400 \text{ V}, I_{C} = 30 \text{ A},$	-	42.4	-	ns
t <sub>f</sub>	Fall Time	$R_G = 6 \Omega$ , $V_{GE} = 15 V$ ,	-	7.2	-	ns
E <sub>on</sub>	Turn-On Switching Loss	Inductive Load, T <sub>C</sub> = 25°C	-	960	-	uJ
E <sub>off</sub>	Turn-Off Switching Loss		-	165	- //	uJ
E <sub>ts</sub>	Total Switching Loss		-	1125	-	uJ
t <sub>d(on)</sub>	Turn-On Delay Time		-	12.8	- \	ns
t <sub>r</sub>	Rise Time		-	27.2	-	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	V <sub>CC</sub> = 400 V, I <sub>C</sub> = 30 A,	-	46.4	-	ns
t <sub>f</sub>	Fall Time	$R_G = 6 \Omega$ , $V_{GE} = 15 V$ ,	-	12.8	-	ns
E <sub>on</sub>	Turn-On Switching Loss	Inductive Load, T <sub>C</sub> = 175°C	-	1430	-	uJ
E <sub>off</sub>	Turn-Off Switching Loss		-	310	-	uJ
E <sub>ts</sub>	Total Switching Loss	1	-	1740	-	uJ

# **Electrical Characteristics of the IGBT** (Continued)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max	Unit
Qg	Total Gate Charge		-	37.4	-	nC
Q <sub>ge</sub>	Gate to Emitter Charge	V <sub>CE</sub> = 400 V, I <sub>C</sub> = 30 A, V <sub>GE</sub> = 15 V	-	7.2	-	nC
Q <sub>gc</sub>	Gate to Collector Charge	1 V GE - 13 V	-	15	-	nC

# Electrical Characteristics of the Diode $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter		Test Condition	ns	Min.	Тур.	Max	Unit	
Ven	V <sub>FM</sub> Diode Forward Voltage	I_ =	3 Δ	T <sub>C</sub> = 25°C	-	1.6	2.3	V	
FM		I <sub>F</sub> = 3 A		$T_{\rm C} = 175^{\rm o}$	-	1.4	-		
E <sub>rec</sub>	Reverse Recovery Energy			T <sub>C</sub> = 175°0	-	29.7	-	uJ	
t	Diode Reverse Recovery Time	V <sub>R</sub> =	= 3 A, dI <sub>F</sub> /dt = 200 A/µs,	$T_{\rm C} = 25^{\rm o}{\rm C}$	/ -	26	-	ns	
'rr	Blodd Novolod Nodovoly Time		V <sub>R</sub> = 400 V	: 400 V	$T_{\rm C} = 175^{\rm o}$	-	153	-	"
Q <sub>rr</sub>	Diode Reverse Recovery Charge			$T_{\rm C} = 25^{\rm o}{\rm C}$	-	35	-	nC	
α <sub>II</sub>	Blodd Nevered Nedevery Change			$T_{\rm C} = 175^{\rm o}$	-	305	-	110	

**Figure 1. Typical Output Characteristics** 

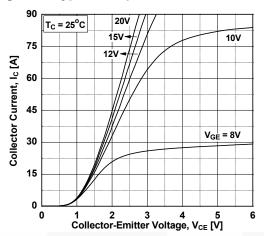


Figure 3. Typical Saturation Voltage Characteristics

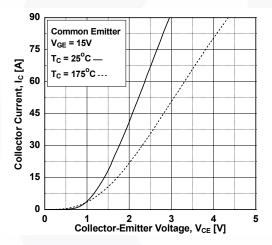
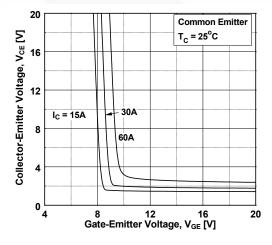


Figure 5. Saturation Voltage vs. V<sub>GE</sub>



**Figure 2. Typical Output Characteristics** 

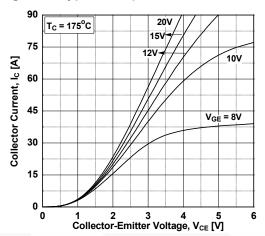


Figure 4. Saturation Voltage vs. Case
Temperature at Variant Current Level

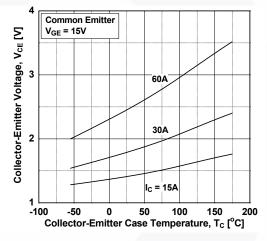


Figure 6. Saturation Voltage vs.  $V_{GE}$ 

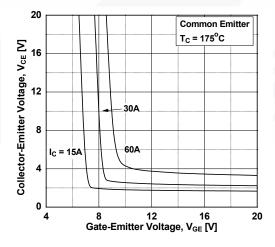


Figure 7. Capacitance Characteristics

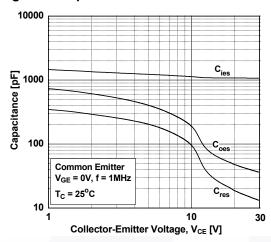


Figure 9. Turn-on Characteristics vs.
Gate Resistance

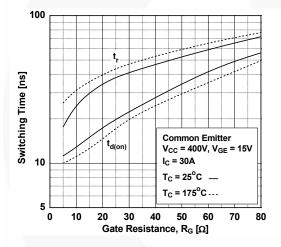


Figure 11. Switching Loss vs.
Gate Resistance

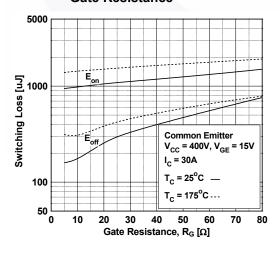


Figure 8. Gate charge Characteristics

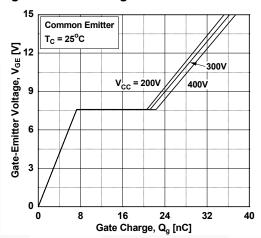


Figure 10. Turn-off Characteristics vs. Gate Resistance

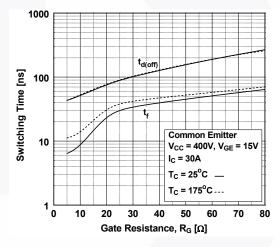


Figure 12. Turn-on Characteristics vs. Collector Current

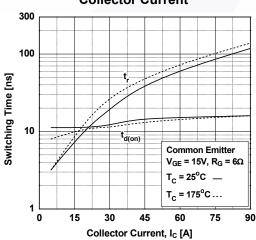
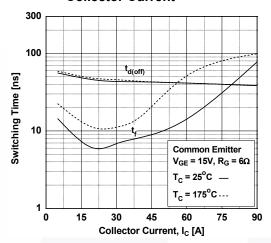


Figure 13. Turn-off Characteristics vs. **Collector Current** 



**Collector Current** 

Figure 14. Switching Loss vs.

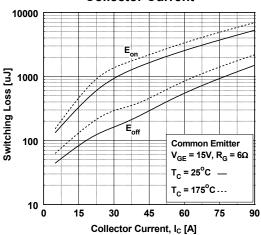


Figure 15. Load Current Vs. Frequency

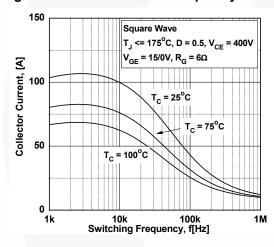


Figure 16. SOA Characteristics

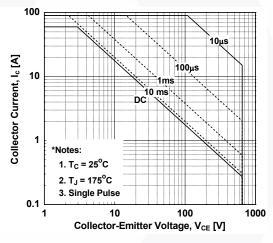


Figure 17. Forward Characteristics

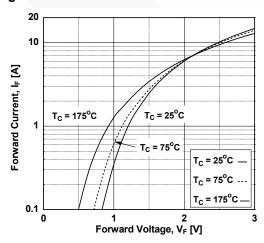


Figure 18. Reverse Recovery Current

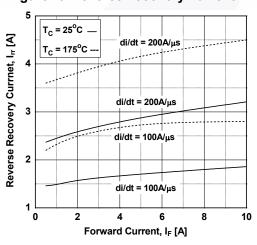


Figure 19. Reverse Recovery Time

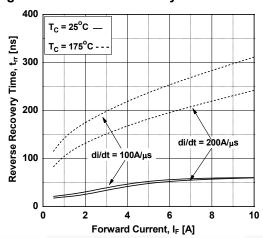


Figure 20. Stored Charge

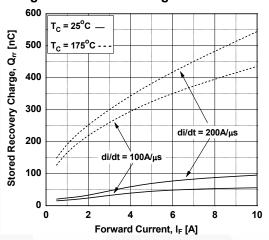


Figure 21. Transient Thermal Impedance of IGBT

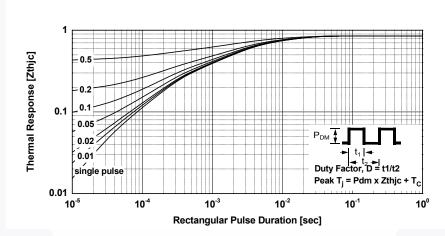
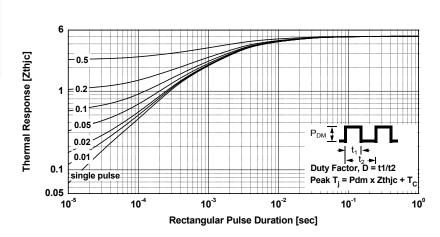
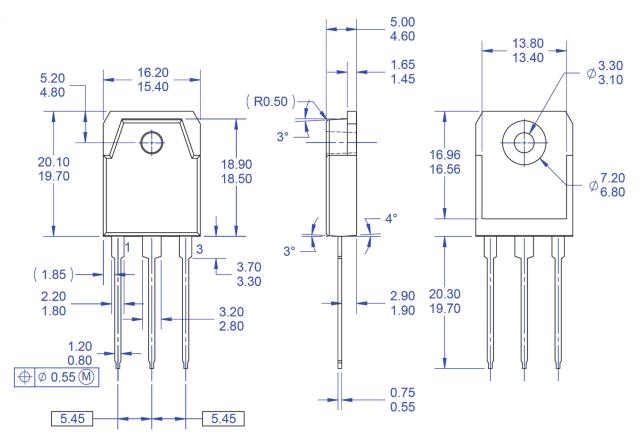


Figure 22. Transient Thermal Impedance of Diode



### **Mechanical Dimensions**



(R0.50) 

- NOTES: UNLESS OTHERWISE SPECIFIED
- A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.
- ALL DIMENSIONS ARE IN MILLIMETERS.
- DIMENSION AND TOLERANCING PER ASME14.5-2009.
- D) DIMENSIONS ARE EXCLUSSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSSIONS. DRAWING FILE NAME: TO3PN03AREV1.
- FAIRCHILD SEMICONDUCTOR.

Figure 23. TO-3P 3L - 3LD, T03, PLASTIC, EIAJ SC-65

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